

substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch;

forming a photoresist film for a photolithographic process on said surface of said wafer; and

forming patterns on said surface of said wafer,

wherein an outer peripheral part of said wafer is chamfered in a thickness direction by mechanical chamfering, and

wherein said connecting portions are chamfered in a plane parallel to said main surface by mechanical chamfering.

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*cont*

15. A process for producing a semiconductor device according to claim 14, further comprising vapor-growing a film on the wafer surface.

16. A process for producing a semiconductor device according to claim 15, further comprising transporting said wafer.

17. A process for producing a semiconductor device according to claim 15, wherein said provided wafer is finished in a mirror wafer state.

5  
18. A process for producing a semiconductor device according to claim  
15, wherein said curved positioning notch does not divide the wafer into several  
sections.

6  
19. A process for producing a semiconductor device according to claim  
15, wherein said curved positioning notch does not cause loss of wafer  
structurable area for electronic components.

7  
20. A process for producing a semiconductor device according to claim  
14, wherein said curved positioning notch does not divide the wafer into several  
sections.

8  
21. A process for producing a semiconductor device according to claim  
14, wherein said curved positioning notch does not cause loss of wafer  
structurable area for electronic components.

9  
22. A process for producing a semiconductor device according to claim  
14, further comprising positioning said wafer by rotating said wafer.

10  
23. A process for producing a semiconductor device according to claim  
22, further comprising positioning said wafer by optical means.

11  
24. A process for producing a semiconductor device according to claim  
14, further comprising transporting said wafer.

12  
25. A process for producing a semiconductor device according to claim  
14, further comprising the step of diffusion.

13  
26. A process for producing a semiconductor device according to claim  
14, further comprising the step of etching.

14  
27. A process for producing a semiconductor device according to claim  
14, wherein said provided wafer is finished in a mirror wafer state.

15  
28. A process for producing a semiconductor device, comprising:  
providing wafer for forming an integrated circuit thereon, the wafer  
having a main surface on which an integrated circuit is to be formed, a  
substantially circular contour portion surrounding said main surface, a curved  
positioning notch formed in said circular contour portion and connecting  
portions defined between said circular contour portion and said curved  
positioning notch;

forming a photoresist film for a photolithographic process on said surface of said wafer; and

forming patterns on said surface of said wafer,

wherein an outer peripheral part of said wafer is chamfered in a thickness direction by grindstone, and

wherein said connecting portions are chamfered in a plane parallel to said main surface by grindstone.

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29. A process for producing a semiconductor device according to claim 28, further comprising vapor-growing a film on the wafer surface.

29. A process for producing a semiconductor device according to claim 29, further comprising transporting said wafer.

29. A process for producing a semiconductor device according to claim 29, wherein said provided wafer is finished in a mirror wafer state.

29. A process for producing a semiconductor device according to claim 29, wherein said curved positioning notch does not divide the wafer into several sections.

20  
33. A process for producing a semiconductor device according to claim  
29, wherein said curved positioning notch does not cause loss of wafer  
structurable area for electronic components.

21  
34. A process for producing a semiconductor device according to claim  
28, wherein said curved positioning notch does not divide the wafer into several  
sections.

22  
35. A process for producing a semiconductor device according to claim  
28, wherein said curved positioning notch does not cause loss of wafer  
structurable area for electronic components.

23  
36. A process for producing a semiconductor device according to claim  
28, further comprising positioning said wafer by rotating said wafer.

24  
37. A process for producing a semiconductor device according to claim  
36, further comprising positioning said wafer by optical means.

25  
38. A process for producing a semiconductor device according to claim  
28, further comprising transporting said wafer.

24  
39. A process for producing a semiconductor device according to claim  
28, further comprising the step of diffusion.

28  
40. A process for producing a semiconductor device according to claim  
28, further comprising the step of etching.

28  
41. A process for producing a semiconductor device according to claim  
28, wherein said provided wafer is finished in a mirror wafer state.

29  
42. A process for producing a semiconductor device comprising:  
providing a wafer for forming an integrated circuit thereon, the wafer  
having a main surface on which an integrated circuit is to be formed, a  
substantially circular contour portion surrounding said main surface, a curved  
positioning notch formed in said circular contour portion and connecting  
portions defined between said circular contour portion and said curved  
positioning notch, wherein said connecting portions are chamfered in a plane  
parallel to said main surface;

forming a photoresist film for a photolithographic process on said surface  
of said wafer; and

forming patterns on said surface of said wafer,

wherein said curved positioning notch does not cause loss of wafer structurable area for electronic components.

*30*  
43. A process for producing a semiconductor device comprising:  
providing a wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch, wherein said connecting portions are chamfered in a plane parallel to said main surface;

forming a photoresist film for a photolithographic process on said surface of said wafer; and

forming patterns on said surface of said wafer,  
wherein said curved positioning notch does not divide the wafer into several sections.

*31*  
44. A process for producing a semiconductor device according to claim 43, wherein said curved positioning notch does not cause loss of wafer structurable area for electronic components.

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Respectfully submitted,

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